

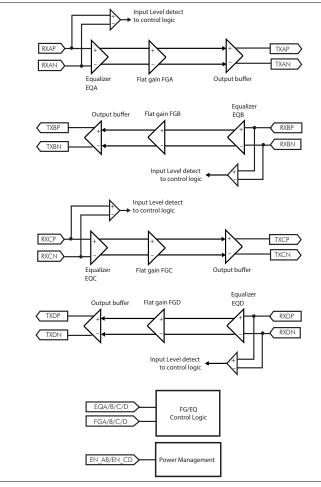


2-Port USB3.1 Gen-2 10Gbps ReDriver

Features

- → 5 & 10Gbps serial link with linear equalizer
- → USB3.1 and USB3.0 Compatible
- → Full Compliancy to USB3.1 Super Speed Standard
- → Four 10Gbps differential signal pairs
- → Pin Adjustable Receiver Equalization
- → Pin Adjustable Flat Gain
- → 100Ω Differential CML I/O's
- ➔ Automatic Receiver Detect
- → Auto "Slumber" mode for adaptive power management
- → Single Supply Voltage: 3.3V
- → Packaging:
 - ◆ 42-pin, TQFN 3.5 x 9mm (ZH42)

Block Diagram



Description

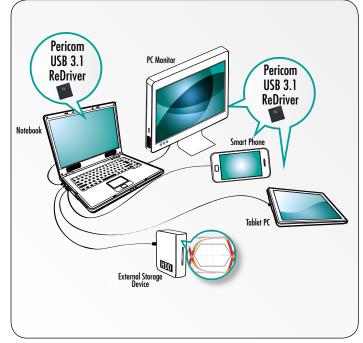
The PI3EQX1004B1 is a low power, high performance 10.0 Gbps 2-Port USB 3.1 linear ReDriver[™] designed specifically for the USB 3.1 protocol.

The device provides programmable equalization, and flat gain to optimize performance over a variety of physical mediums by reducing Inter-Symbol Interference. PI3EQX1004B1 supports two 100Ω Differential CML data I/O's between the Protocol ASIC to a switch fabric, over cable, or to extend the signals across other distant data pathways on the user's platform.

The integrated equalization circuitry provides flexibility with signal integrity of the signal before the ReDriver. Each channel operates fully independently. The channels' input signal level determines whether the output is active.

The PI3EQX1004B1 also includes an automatic receiver detect function. The receiver detection loop will be active again if the corresponding channel's signal detector is idle for longer than 7.3ms. The channel will then move to Unplug Mode if load not detected, or it will return to Low Power Mode (Slumber Mode) due to inactivity.

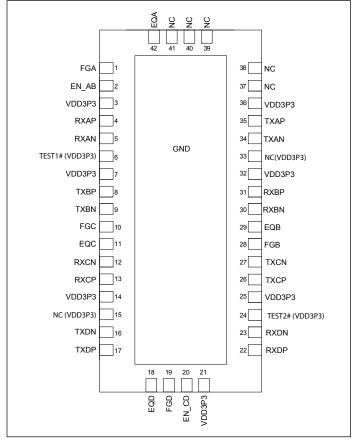
Figure1







Pin Diagram (42-pin, TQFN 3.5x9mm) ZH42







Pin #	Pin Name	Туре	Description
3, 7, 14, 21, 25, 32, 36	VDD	Power	3.3V power supply, +/-0.3V
1, 28	FGA, FGB	Innut	The DC flat gain selection. 4-level input pins. With internal 100k Ω pull-up
10, 19	FGC, FGD	Input	resistor and 200k Ω pull-down resistor.
42, 29	EQA, EQB	Input	The EQ selection. 4-level input pins. With internal $100k\Omega$ pull-up resistor and
11, 18	EQC, EQD	Input	200kΩ pull-down resistor.
4, 5	RXAP, RXAN		
31, 30	RXBP, RXBN	Innut	CML input terminals. With selectable input termination between 50 Ω to VDD,
13, 12	RXCP, RXCN	Input	67kΩ to VbiasRx or 67 kΩ to GND.
22, 23	RXDP, RXDN		
35, 34	TXAP, TXAN		
8, 9	TXBP, TXBN	Output	CML output terminals. With selectable output termination between 50 Ω to
26, 27	TXCP, TXCN	Output	VDD, $6k\Omega$ to VDD, $6k\Omega$ to VbiasTx or Hi-Z.
17, 16	TXDP, TXDN		
2	EN_AB		Channel Enable. With internal 300k Ω pull-up resistor.
20	EN_CD	Input	"High" – Channel is in normal operation.
20	EN_CD		"Low" – Channel is in power down mode.
Center Pad	GND	GND	Supply Ground
6	Test1#	Innut	Connect to VDD is recommended
24	Test2#	Input	Connect to VDD is recommended
15, 33	NC	NC	NC pin connect to VDD is recommended
37, 38, 39, 40, 41	NC	NC	NC

Pin Description (42-pin, TQFN 3.5x9mm)

Power Management

Notebooks, netbooks, and other power sensitive consumer devices require judicious use of power in order to maximize battery life. In order to minimize the power consumption of our devices, Diodes has added an additional adaptive power management feature. When a signal detector is idle for longer than 1.3ms, the corresponding channel will move to low power mode ONLY. (It means both channels will move to low power mode individually).

In the low power mode, the signal detector will still be monitoring the input channel. If a channel is in low power mode and the input signal is detected, the corresponding channel will wake-up immediately. If a channel is in low power mode and the signal detector is idle longer than 6ms, the receiver detection loop will be active again. If load is not detected, then the Channel will move to Device Unplug Mode and monitor the load continuously. If load is detected, it will return to Low Power Mode and receiver detection will be active again per 6ms.

Operating Modes

Mode	R _{IN}	R _{OUT}
PD	$67 \mathrm{k}\Omega$ to GND	HIZ
Unplug Mode	$67 \mathrm{k}\Omega$ to VbiasRx	6kΩ to VbiasTx
Deep Slumber Mode	50Ω to Vdd	6kΩ to VbiasTx
Slumber Mode	50Ω to Vdd	$6k\Omega$ to Vdd
Active Mode	50Ω to Vdd	50Ω to Vdd





Equalization Setting:

EQA/B/C/D are the selection pins for the equalization selection

	Equalizer setting (dB)		
EQA/B/C/D	@2.5GHz	@5GHz	
0 (Tie 0Ω to GND)	6.7	12.4	
R (Tie Rext to GND)	3.5	8.0	
F (Leave Open)	5.3	10.6	
1 (Tie 0Ω to VDD)	8.4	14.6	

Flat Gain Setting:

FGA/B/C/D are the selection pins for the DC gain

	Flat Gain Settings
FGA/B/C/D	dB
0 (Tie 0Ω to GND)	-1.6
R (Tie Rext to GND)	-0.5
F (Leave Open)	1.0
1 (Tie 0Ω to VDD)	2.7

Channel Enable Setting:

EN_AB/EN_CD are the channel enable pins for channels A&B and C&D respectively

	Channel Enable Setting
EN	Setting
0	Disabled
1	Enabled (Default)





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.) Note:

, , , , ,	0 1 1
Storage Temperature	65°C to +150°C
Supply Voltage to Ground Potential	-0.5V to +3.8V
DC SIG Voltage	$-0.5V$ to $V_{DD} + 0.5V$
Output Current	–25mA to +25mA
ESD, Human Body Model	-2kV to +2kV
Power Dissipation Continuous	
Max Junction Temperature	

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Control pin Specifications (VDD = 3.3 ± 0.3 V TA = 0 to 70°C)

Symbol	Parameter	Min.	Тур.	Max.	Units		
2-level contro	-level control pins						
V _{IH}	DC input logic High	VDD*0.65			V		
V _{IL}	DC input logic Low			VDD*0.35	V		
I _{IH}	Input High current			25	uA		
I _{IL}	Input Low current	-25			uA		
4-level contro	4-level control pins						
V _{IH}	DC input logic "High"	0.92*VDD	VDD		V		
V _{IF}	DC input logic "Float"	0.59*VDD	0.67*VDD	0.75*VDD	V		
V _{IR}	DC input logic "With Rext to GND"	0.25*VDD	0.33*VDD	0.41*VDD	V		
V _{IL}	DC input logic "Low"		GND	0.08*VDD	V		
I _{IH}	Input High current			50	uA		
I _{IL}	Input Low current	-50			uA		
Rext	External resistor connects to GND ($\pm 5\%$)	64.6	68	71.4	kΩ		

AC/DC Electrical Characteristics (VDD = 3.3 ± 0.3 V TA = 0 to 70°C)

Power and Latency							
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
V _{dd-3.3}	Supply voltage		3.0	3.3	3.6	V	
I _{active}	Active mode current consumption	EN_AB & EN_CD = 1, 10Gbps, compli- ance test pattern		260	334	mA	
I _{slumber}	Slumber mode current consumption	EN_AB & EN_CD = 1, no input signal longer than $T_{slumber}$		32	38		
I _{DeepSlumber}	Deep slumber mode current con- sumption	EN_AB & EN_CD = 1 no input signal longer than T _{DeepSlumber}		0.8	1.2	mA	
I _{unplug}	Unplug mode current consumption	EN_AB & EN_CD = 1, no output load is detected		0.6	0.9		
I _{pd}	Power down mode current consump- tion	$EN_AB \& EN_CD = 0$		20	100	μA	
t _{pd}	Latency	From input to output			2	ns	





AC/DC Electrical Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
CML Receiver In	put (100 Ω differential)					
Receiver Electrica	l Specification					
C _{rxparasitic}	The parasitic capacitor for RX				1.0	pF
R _{RX-DIFF-DC}	DC Differential Input Impedance		72		120	
R _{RX-SINGLE_DC}	DC single ended input impedance	DC impedance limits are need to guar- antee RxDet. Measured with respect to GND over a voltage of 500mV max	18		30	Ω
Z _{RX-HIZ-DC-PD}	DC input CM input impedance for V>0 during reset or power down	(Vcm=0 to 500mV)	25			kΩ
Cac_coupling	AC coupling capacitance		75		265	nF
V _{RX-CM-AC-P}	Common mode peak voltage	AC up to 5GHz			150	mVpeak
V _{RX-CM-DC-Ac-} tive-Idle-Delta-P	Common mode peak voltage Avguo(V _{TX-D+} + V _{TX-D-})/2-Avgu1(V _{TX-D+} + V _{TX-D-})/2	Between U0 and U1. AC up to 5GHz			200	mVpeak
Transmitter Elect	rical Specification					
V _{TX-DIFF-PP}	Ouput differential p-p voltage swing	Differential Swing V _{TX-D+} -V _{TX-D-}			1.2	Vppd
R _{TX-DIFF-DC}	DC Differential TX Impedance		72		120	Ω
V _{TX-RCV-DET}	The amount of voltage change al- lowed during RxDet				600	mV
Cac_coupling	AC coupling capacitance		75		265	nF
T _{TX-EYE} (10Gbps)	Transmitter eye, Include all jittter	At the silicon pad. 10Gbps	0.646			UI
T _{TX-EYE} (5Gbps)	Transmitter eye, Include all jittter	At the silicon pad. 5Gbps	0.625			UI
T _{TX-DJ-} DD(10Gbps)	Transmitter deterministic jittter	At the silicon pad. 10Gbps			0.17	UI
T _{TX-DJ-DD(5Gbps)}	Transmitter deterministic jittter	At the silicon pad. 5Gbps			0.205	UI
C _{txparasitic}	The parasitic capacitor for TX				1.1	pF
R _{TX-DC-CM}	Common mode DC output Imped- ance		18		30	Ω
V _{TX-DC-CM}	The instantaneous allowed DC com- mon mode voltage at the connector side of the AC coupling capacitors	V _{TX-D+} +V _{TX-D-} /2	0		2.2	V
V _{TX-C}	Common-Mode Voltage	V _{TX-D+} +V _{TX-D-} /2	VDD- 2V		VDD	V
V _{TX-CM-AC-PP-} Active	Active mode TX AC common mode voltage	$V_{TX\text{-}D\text{+}}\text{+}V_{TX\text{-}D\text{-}}$ for both time and amplitude			100	mVpp
V _{TX-CM-DC-} Active_Idle-Delta	Common mode delta voltage Avguo(V _{TEX-D+} + V _{TX-D-}])/2-Avgu1(V _{TX-D+} + V _{TX-D-}])/2	Between U0 to U1			200	mV-peak





AC/DC Electrical Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VTX-Idle-Diff-AC- pp	Idle mode AC common mode delta voltage V _{TX-D+} -V _{TX-D-}	Between Tx+ and Tx- in idle mode. Use the HPF to remove DC components. =1/ LPF. No AC and DC signals are applied to Rx terminals.			10	mVppd
V _{TX-Idle-Diff-DC}	Idle mode DC common mode delta voltage V _{TX-D+} -V _{TX-D-}	Between Tx+ and Tx- in idle mode. Use the LPF to remove DC components. =1/ HPF. No AC and DC signals are applied to Rx terminals.			10	mV
Channel Perform	ance					
Gp	Peaking gain (Compensation at 5GHz, relative to 100MHz, 100mV _{p-p} sine wave input)	EQx=0 EQx=R EQx=F EQx=1		12.4 8.0 10.6 14.6		dB
		Variation around typical	-3		+3	dB
G _F	Flat gain (100MHz, EQx=F)	FQx=0 FQx=R FQx=F FQx=1 Variation around typical	-3	-1.6 -0.5 1.0 2.7	+3	dB dB
V _{SW_100M}	-1dB compression point output swing (at 100MHz)			1000		mVppd
V _{SW_5G}	-1dB compression point output swing (at 5GHz)			850		mVppd
DDNEXT	Differential near-end crosstalk ¹	100MHz to 5GHz, Figure2		-40		dB
V	Input referred ratio	100MHz to 5GHz, FGx=1, EQx=R, Figure 3		0.6		
Vnoise-input	Input-referred noise	100MHz to 5GHz, FGx=1, EQx=1, Figure 3		0.5		mV _{RMS}
\$7	Output of the interaction	100MHz to 5GHz, FGx=1, EQx=R, Figure 3		0.8		
Vnoise-output	Output-referred noise ²	100MHz to 5GHz, FGx=1, EQx=1, Figure 3		1		mV _{RMS}
Signal and Frequ	ency Detectors	·				
V _{th_upm}	Unplug mode detector threshold	Threshold of LFPS when the input impedance of the redriver is 67kohm to VbiasRx only. Used in the unplug mode.	200		800	mVppd
V _{th_dsm}	Deep slumber mode detector threshold	LFPS signal threshold in Deep slumber mode	100		600	mVppd





AC/DC Electrical Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{th_am}	Active mode detector threshold	Signal threshold in Active and slumber mode	45		175	mVppd
F _{th}	LFPS frequency detector	Detect the frequency of the input CLK pattern	100		400	MHz

Note:

1. Measured using a vector-network analyzer (VNA) with -15dBm power level applied to the adjacent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with 50Ω .

2. Guaranteed by design and characterization.

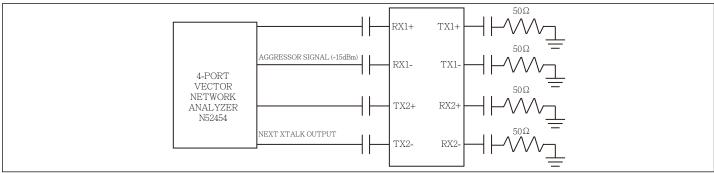


Figure2. Channel-isolation test configuration

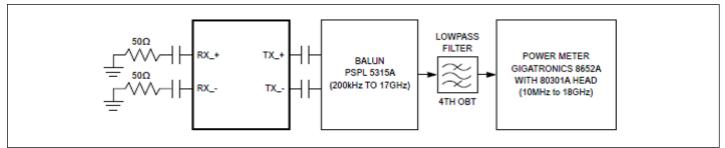


Figure3. Noise test configuration

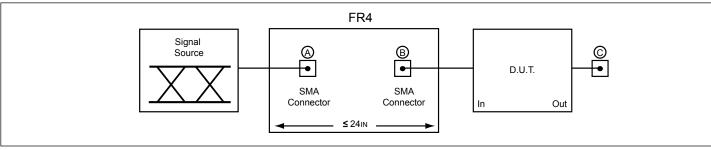
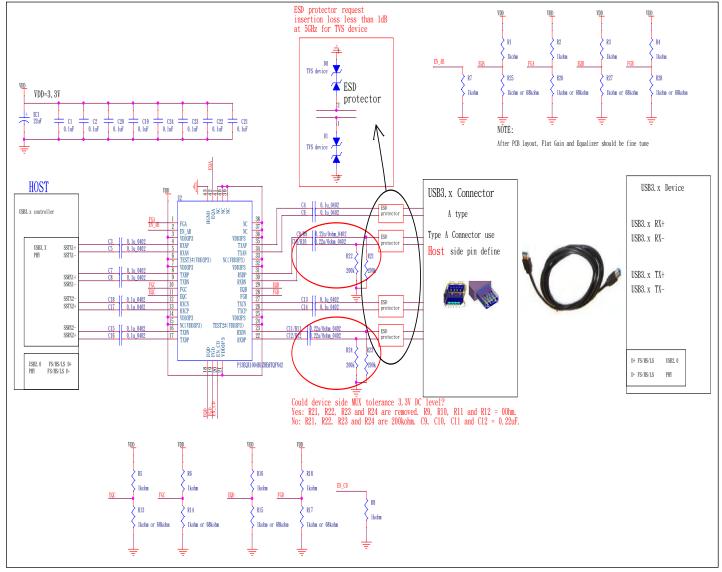


Figure4. Test Condition Referenced in the Electrical Characteristic Table





Application Schematics



Part Marking

ZH Package

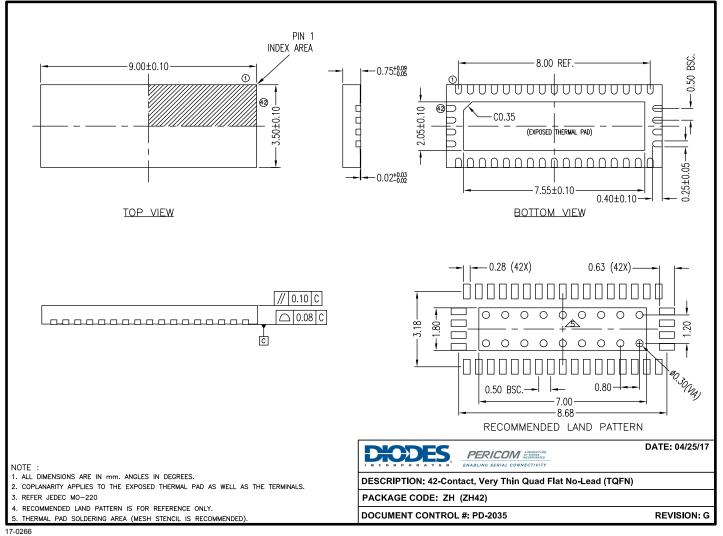


YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code





Packaging Mechanical: 42-TQFN (ZH)



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

	Ordering Number	Package Code	Package Description
PI3EQX1004B1ZHEX ZH 42-contact, Very Thin Quad Flat No-Lead (TQFN)	PI3EQX1004B1ZHEX	ZH	42-contact, Very Thin Quad Flat No-Lead (TQFN)

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/

3. E = Pb-free and Green

4. X suffix = Tape/Reel





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